

EVLYS LTD. - POWER SEMICONDUCTORS DEVICES - Wholesale and Retail.

Phase Control Disc Thyristor Type DT70-1600-28

High power cycling capability / Low on-state and switching losses
Designed for traction and industrial applications

Mean on-state current		I _{TAV}		1600 A	
Repetitive peak off-state voltage		V _{DRM}		2000 ÷ 2800 V	
Repetitive peak reverse voltage		V _{RRM}			
Turn-off time		t _q		320 μs	
V _{DRM} , V _{RRM} , V	2000	2200	2400	2600	2800
Voltage code	20	22	24	26	28
T _j , °C	- 60 ÷ 125				

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I _{TAV}	Mean on-state current	A	1600 2120	T _c = 99 °C, Double side cooled T _c = 85 °C, Double side cooled 180° half-sine wave; 50 Hz	
I _{TRMS}	RMS on-state current	A	2512	T _c = 99 °C, Double side cooled 180° half-sine wave; 50 Hz	
I _{TSM}	Surge on-state current	kA	38.0 44.0	T _j =T _{jmax} T _j =25 °C	180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _D =V _R =0 V; Gate pulse: I _G =2 A; t _{GP} =50 μs; di _G /dt≥1 A/μs
			40.0 46.0	T _j =T _{jmax} T _j =25 °C	180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _D =V _R =0 V; Gate pulse: I _G =2 A; t _{GP} =50 μs; di _G /dt≥1 A/μs
I ² t	Safety factor	A ² s·10 ³	7220 9680	T _j =T _{jmax} T _j =25 °C	180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _D =V _R =0 V; Gate pulse: I _G =2 A; t _{GP} =50 μs; di _G /dt≥1 A/μs
			6640 8780	T _j =T _{jmax} T _j =25 °C	180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _D =V _R =0 V; Gate pulse: I _G =2 A; t _{GP} =50 μs; di _G /dt≥1 A/μs
BLOCKING					
V _{DRM} , V _{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	2000÷2800	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; 50 Hz; Gate open	
V _{DSM} , V _{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	2100÷2900	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; 50 Hz; single pulse; Gate open	
V _D , V _R	Direct off-state and Direct reverse voltages	V	0.75·V _{DRM} 0.75·V _{RRM}	T _j =T _{jmax} ; Gate open	

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TRIGGERING				
I_{FGM}	Peak forward gate current	A	8	$T_j = T_{j\ max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	5	$T_j = T_{j\ max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/ μ s	630	$T_j = T_{j\ max}$; $V_D = 0.67 \cdot V_{DRM}$; $I_{TM} = 2 I_{TAV}$; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ μ s; $di_G/dt \geq 1$ A/ μ s
THERMAL				
T_{stg}	Storage temperature	$^{\circ}$ C	-60 ÷ 125	
T_j	Operating junction temperature	$^{\circ}$ C	-60 ÷ 125	
MECHANICAL				
F	Mounting force	kN	33.0 ÷ 40.0	
a	Acceleration	m/s^2	50 100	Device unclamped Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V_{TM}	Peak on-state voltage, max	V	1.75	$T_j = 25$ $^{\circ}$ C; $I_{TM} = 5000$ A
$V_{T(TO)}$	On-state threshold voltage, max	V	0.85	$T_j = T_{j\ max}$; $0.5 \pi I_{TAV} < I_T < 1.5 \pi I_{TAV}$
r_T	On-state slope resistance, max	$m\Omega$	0.200	
I_L	Latching current, max	mA	1500	$T_j = 25$ $^{\circ}$ C; $V_D = 12$ V; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ μ s; $di_G/dt \geq 1$ A/ μ s
I_H	Holding current, max	mA	300	$T_j = 25$ $^{\circ}$ C; $V_D = 12$ V; Gate open
BLOCKING				
I_{DRM}, I_{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	200	$T_j = T_{j\ max}$; $V_D = V_{DRM}$; $V_R = V_{RRM}$
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage ¹⁾ , min	V/ μ s	1000	$T_j = T_{j\ max}$; $V_D = 0.67 \cdot V_{DRM}$; Gate open
TRIGGERING				
V_{GT}	Gate trigger direct voltage, max	V	5.00	$T_j = T_{j\ min}$ $T_j = 25$ $^{\circ}$ C $T_j = T_{j\ max}$ $V_D = 12$ V; $I_D = 3$ A; Direct gate current
			3.00	
2.00				
I_{GT}	Gate trigger direct current, max	mA	500	$T_j = T_{j\ min}$
			300	$T_j = 25$ $^{\circ}$ C
			200	$T_j = T_{j\ max}$
V_{GD}	Gate non-trigger direct voltage, min	V	0.35	$T_j = T_{j\ max}$; $V_D = 0.67 \cdot V_{DRM}$;
I_{GD}	Gate non-trigger direct current, min	mA	15.00	Direct gate current
SWITCHING				
t_{gd}	Delay time	μ s	4.00	$T_j = 25$ $^{\circ}$ C; $V_D = 0.4 \cdot V_{DRM}$; $I_{TM} = I_{TAV}$; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ μ s; $di_G/dt \geq 1$ A/ μ s
t_q	Turn-off time ²⁾ , max	μ s	400	$dv_D/dt = 50$ V/ μ s; $T_j = T_{j\ max}$; $I_{TM} = 2000$ A; $di_R/dt = -10$ A/ μ s; $V_R = 100$ V; $V_D = 0.67 V_{DRM}$;

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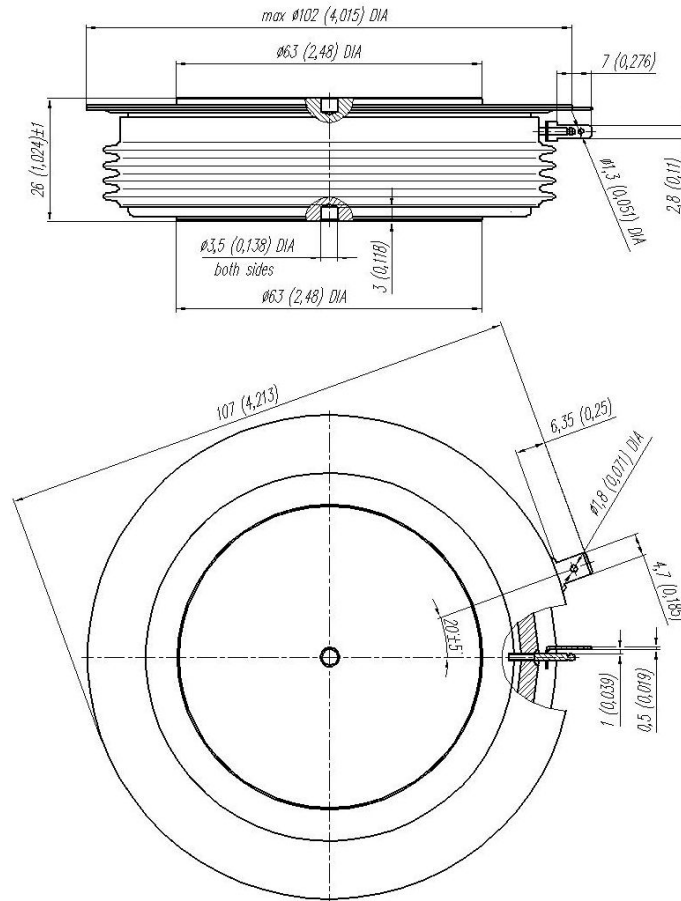
THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.0100	Direct current	Double side cooled
R_{thjc-A}			0.0220		Anode side cooled
R_{thjc-K}			0.0180		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0030	Direct current	
MECHANICAL					
w	Weight, typ	g	1000		
D_s	Surface creepage distance	mm (inch)	36.50 (1.437)		
D_a	Air strike distance	mm (inch)	16.5 (0.650)		

PART NUMBERING GUIDE				
DT	70	1600	28	
1	2	3	4	
1. DT - Phase Control Disc Thyristor 2. Element Diameter 3. Mean on-state current, A 4. Voltage code				

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OVERALL DIMENSIONS

Package type: T.E3



All dimensions in millimeters (inches)